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APPLICATION NO.	F	ILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/116,138 07/15/1998		07/15/1998	JOHN MARK ANTHONY	TI-24953	2214	
23494	7590	12/16/2003		EXAMINER		
TEXAS IN P O BOX 65		ENTS INCORPOR	COLEMAN, WILLIAM D			
DALLAS, T			ART UNIT •	PAPER NUMBER		
				2823		

Please find below and/or attached an Office communication concerning this application or proceeding.

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, , ,		Appl	ication No.	Applicant(s)							
Office Action Commons			16,138	ANTHONY ET AL							
Office Action Summary		Exan	nin r	Art Unit							
			avid Coleman	2823							
	Th MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply										
THE I - Exter after - If the - If NO - Failu - Any r	ORTENED STATUTORY PERIOD IN MAILING DATE OF THIS COMMUNISIONS of time may be available under the provision SIX (6) MONTHS from the mailing date of this comperiod for reply specified above is less than thirty period for reply is specified above, the maximum are to reply within the set or extended period for repeply received by the Office later than three months in different adjustment. See 37 CFR 1.704(b).	IICATION. s of 37 CFR 1.136(a). In munication. 30) days, a reply within the statutory period will apply by will, by statute, cause the	no event, however, may ne statutory minimum of the and will expire SIX (6) Mo ne application to become	a reply be timely filed nirty (30) days will be considered timel DNTHS from the mailing date of this co ABANDONED (35 U.S.C. § 133).	ly. ommunication.						
1)🖂	Responsive to communication(s) fi	ed on 20 August 2	<u> 2002</u> .								
2a) <u></u> ☐	This action is FINAL.	2b)⊠ This action	is non-final.								
3)□	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.										
Disposition of Claims											
4)⊠	☑ Claim(s) <u>1-30,36-40 and 46-80</u> is/are pending in the application.										
•	4a) Of the above claim(s) <u>2-40 and 46-80</u> is/are withdrawn from consideration.										
5)[Claim(s) is/are allowed.										
6)⊠	Claim(s) 1 is/are rejected.										
7)⊠	Claim(s) 26,27 and 30 is/are objected to.										
8)□	Claim(s) are subject to restr	iction and/or elect	ion requirement.								
Applicati	on Papers										
9)	The specification is objected to by t	he Examiner.									
10)	The drawing(s) filed on is/are: a) □ accepted or b) □ objected to by the Examiner.										
	Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).										
	Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).										
11)⊠ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.											
Priority under 35 U.S.C. §§ 119 and 120											
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 13) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application) since a specific reference was included in the first sentence of the specification or in an Application Data Sheet. 37 CFR 1.78. a) The translation of the foreign language provisional application has been received. 14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121 since a specific reference was included in the first sentence of the specification or in an Application Data Sheet. 37 CFR 1.78.											
Attachmen	t(s)										
2) Notic	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review mation Disclosure Statement(s) (PTO-1449)			v Summary (PTO-413) Paper No(f Informal Patent Application (PT0							

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DETAILED ACTION

Response to Amendment

1. Applicant's request for reconsideration of the finality of the rejection of the last Office action is persuasive and, therefore, the finality of that action is withdrawn.

Response to Arguments

- 2. Applicant's arguments filed August 20, 2002 have been fully considered but they are not persuasive.
- 3. Applicants contend that Hsieh, U.S. Patent 4,432,035 herein known as Hsieh fails to anticipate claim 1 because claim 1 is limited to method of fabricating a field-effect device.
- 4. In response to Applicants contention that Hsieh fails to teach each and every limitation of claim1, the Examiner objects to Applicants Oath & Declaration because an inventor swears that he/she is the first to invent or make an improvement, however in light of the arguments, it is well known that William Shockley, Walter Brattain and John Bardeen built the first working transistor and they are not listed on the Oath and Declaration. It appears that Applicants arguments are sincere, however, there is no possible way that Applicants could make a claim for an invention and argue that Hsieh's invention is not a field effect device having a gate electrode. The Examiner provides Applicants with supplemental citations (*Device Electronics For Integrated Circuits*, 2nd Ed., Muller et al., John Wiley & Sons, © 1986 "The Biographical Dictionary of Scientists, 3rd edition, vol. 1, Oxford University Press, NY, © 1984/1985 for scientist and engineers, pp. 120-121) to show that it is well known that a MOS device is a field effect device having a gate electrode, and that Shockley, Brattain and Bardeen were the first to disclose the field effect device.

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5. Applicants contend that the MOS system of Hsieh does not disclose forming a conductive

gate overlying the metal silicate dielectric layer.

6. In response to Applicants contention that Hsieh fails to disclose forming a conductive

gate overlying the metal silicate dielectric layer, please see FIG. 2 where a conductive gate 12' is

formed overlying the metal silicate dielectric layer. Applicants arguments reveal that they could

not possibly possess the claimed invention due to the lack of understanding of Silicon

Technology and the MOS system. These arguments are not expected from inventors experienced

with an understanding of integrated circuits incorporating silicon technology.

Claim Rejections - 35 USC § 102

7. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the

basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claim 1 is rejected under 35 U.S.C. 102(b) as being anticipated by Hsieh et al., U.S.

Patent 4,432,035.

8.

9. <u>Hsieh discloses a semiconductor process as claimed.</u> See FIGS. 1-8, where <u>Hsieh</u>

substantially teaches the claimed invention.

10. Hsieh teaches a method of fabricating a field-effect device on an integrated circuit,

comprising the steps of:

providing a single-crystal silicon substrate;

forming a metal silicate dielectric layer 12' on the substrate 10; and

forming a conductive gate 14 overlying the metal silicate dielectric layer.

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Objection

11. Claims 26, 27 and 30 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Conclusion

- 12. Any inquiry concerning this communication or earlier communications from the examiner should be directed to W. David Coleman whose telephone number is 703-305-0004. The examiner can normally be reached on 9:00 AM-5:00 PM. After February 4, 2004 please call 571-272-1856.
- 13. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on 703-306-2794. The fax phone number for the organization where this application or proceeding is assigned is 703-308-7722.
- 14. Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

. David Coleman_

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Primary Examiner

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